





TEXAS INSTRUMENTS

TXV0106-Q1 SCES956B – AUGUST 2023 – REVISED FEBRUARY 2024

TXV0106-Q1 Automotive 6-Bit Fix Direction Low-Skew, Low-Jitter Voltage Translator or Buffer

1 Features

- Configurable design allows each port to operate with a power supply range from 1.14 V to 3.6 V
- Supports up to 500Mbps for 1.65 V to 3.6 V
- AEC-Q100 qualified for automotive applications
- Meets RGMII 2.0 timing specifications:
 - < 750 ps rise and fall time</p>
 - < ± 5 % duty cycle distortion
 - < ± 400 ps channel to channel skew
 - Up to 250Mbps/channel
- Integrated 10 Ω damping output resistor to minimize signal reflections
- High drive strength (up to 12 mA at 3.6 V)
- Fully configurable symmetric dual-rail design
- Optimal signal integrity performance with 390ps peak-to-peak jitter for 1.8 V to 3.3 V
- Features V_{CC} isolation and V_{CC} disconnect
- I_{off} supports partial-power-down mode operation
- Latch-up performance exceeds 100 mA per JESD 78, Class II
- ESD protection exceeds JESD 22:
 - 2000-V Human-Body Model
 - 1000-V Charged-Device Model
- Low power consumption:
 - 10-µA maximum (25°C)
 - 20-µA maximum (–40°C to 125°C)
- Operating temperature from –40°C to +125°C
- Available in wettable flank WQFN (BQB) package

2 Applications

- Medium or short range radar
- ADAS domain controller
- HVAC controller design
- Machine vision camera
- Rack sever motherboard
- IP telephone

3 Description

The TXV0106-Q1 is a 6-bit, dual-supply fixeddirection low-skew, low jitter voltage translation device. This device can be used for redriving, voltage translation and power isolation when implementing skew sensitive interface, such as RGMII between Ethernet MAC and PHY. The Ax I/O pins and enable pin (\overline{OE}) are referenced to V_{CCA} logic levels, and Bx I/O pins are referenced to V_{CCB} logic levels. This device has improved channel-to-channel skew, duty cycle distortion and symmetric rise or fall timing for applications requiring strict timing conditions.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, thus preventing damaging current backflow through the device when it is powered down.

The V_{CC} isolation feature is designed so that if either V_{CC} supply is at or near 0 V both ports will switch to a high-impedance state. This feature enables power isolation for communications across multiple MACs and PHYs, and is beneficial in situations where MACs and PHYs are powered up asynchronously preventing current backflow between devices.

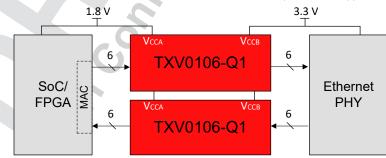
The TXV0106-Q1 transmits data in a fixed direction from the A bus to the B bus. When \overline{OE} is set to High, both Ax and Bx pins will be forced into a highimpedance state. See *Device Functional Modes* for a summary of the operation of the control logic.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾									
TXV0106-Q1	BQB (WQFN, 16)	3.5 mm × 2.5 mm									

(1) For more information see, Section 11.

 The package size (length × width) is a nominal value and includes pins, where applicable.



TXV0106-Q1 in RGMII Applications

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



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4 Pin Configuration and Functions

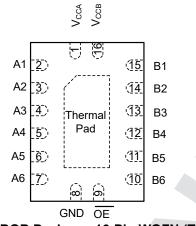


Figure 4-1. BQB Package, 16-Pin WQFN (Top View)

Table 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION					
NAME	NO.		DESCRIPTION					
V _{CCA}	1	_	A-port supply voltage. 1.8 V \leq V _{CCA} \leq 3.6 V.					
A1	2	I/O	Input/output A1. Referenced to V _{CCA} .					
A2	3	I/O	Input/output A2. Referenced to V _{CCA} .					
A3	4	I/O	Input/output A3. Referenced to V _{CCA} .					
A4	5	I/O	Input/output A4. Referenced to V _{CCA} .					
A5	6	I/O	Input/output A5. Referenced to V _{CCA} .					
A6	7	I/O	Input/output A6. Referenced to V _{CCA} .					
GND	8	—	Ground.					
ŌE	9	I	Output Enable. Pull to GND to enable all outputs. Pull to V_{CCA} to place all outputs in high-impedance mode. Referenced to V_{CCA} .					
B6	10	I/O	Input/output B6. Referenced to V _{CCB} .					
B5	11	I/O	Input/output B5. Referenced to V _{CCB} .					
B4	12	I/O	Input/output B4. Referenced to V _{CCB} .					
B3	13	I/O	Input/output B3. Referenced to V _{CCB} .					
B2	14	I/O	Input/output B2. Referenced to V _{CCB} .					
B1	15	I/O	Input/output B1. Referenced to V _{CCB} .					
V _{CCB}	16	-	B-port supply voltage. 1.8 V \leq V _{CCB} \leq 3.6 V.					
Thermal pad	·	_	Thermal pad. Can be grounded (recommended) or left floating.					

(1) I = input, O = output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CCA}	Supply voltage A		-0.5	4.6	V
V _{CCB}	Supply voltage B		-0.5	4.6	V
		I/O Ports (A Port)	-0.5	4.6	
VI	Input Voltage ⁽²⁾	I/O Ports (B Port)	-0.5	4.6	V
		Control Inputs	-0.5	4.6	
V	Voltage applied to any output in the high-impedance or power-off	A Port	-0.5	4.6	V
Vo	state ⁽²⁾	B Port	-0.5	4.6	V
	Valtage explicit to any output in the high or law state(2) (3)	A Port	-0.5 V _{CC}	_A + 0.5	V
Vo	Voltage applied to any output in the high or low state ^{(2) (3)}	B Port	-0.5 V _{CCB} +		V
I _{IK}	Input clamp current	V ₁ < 0	-50		mA
I _{OK}	Output clamp current	V _O < 0	-50		mA
I _O	Continuous output current		_50	50	mA
	Continuous current through V _{CC} or GND		-100	100	mA
Tj	Junction Temperature			150	°C
T _{stg}	Storage temperature	9	-65	150	°C

(1) Operation outside the Absolute Maximum Rating may cause permanent device damage. Absolute Maximum Rating do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Rating, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.

5.2 ESD Ratings

			VALUE	UNIT	
V	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD classification level 2	±2000	V	
V _(ESD)		Charged device model (CDM), per AEC Q100-011 CDM ESD classification level C3	±1000	V	

(1) AEC Q100-002 indicates that HBM stressing must be in accordance with the ANSI/ESDA/JEDEC JS-001 specification



5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

				MIN	MAX	UNIT		
V _{CCA}	Supply voltage A			1.14	3.6	V		
V _{CCB}	Supply voltage B			1.14	3.6	V		
V _{IH}	High-level input voltage	Data Inputs (Ax, Bx), OE (Referenced to V _{CCI})	V _{CCI} = 1.14 V - 3.6 V	V _{CCI} x 0.7		V		
V _{IL}	Low-level input voltage	Data Inputs (Ax, Bx), $\overline{\text{OE}}$ (Referenced to V _{CCI})	V _{CCI} = 1.14 V - 3.6 V		V _{CCI} x 0.3	V		
		·	V _{CCO} = 1.14 V		-3			
I _{OH}			V _{CCO} = 1.65 V - 1.95 V		mA			
	High-level output cu	inent	V _{CCO} = 2.3 V - 2.7 V	-9				
				-12				
			V _{CCO} = 1.14 V		3			
			V _{CCO} = 1.65 V - 1.95 V		8			
I _{OL}	Low-level output cu	rrent	V _{CCO} = 2.3 V - 2.7 V		9	9 mA		
			.0	12				
VI	Input voltage			0	3.6	V		
\ <i>\</i>	Outrutualtaria	Active State		0	V _{CCO}	V		
Vo	Output voltage	Tri-State		0	3.6	v		
Δt/Δv	Input transition rise	and fall time		5	5	ns/V		
T _A	Operating free-air to	emperature	-40	125	°C			

(1) V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port.

5.4 Thermal Information

		TXV0106 / TXV0106-Q1	
	THERMAL METRIC ⁽¹⁾	BQB (WQFN)	UNIT
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	71.0	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	64.5	°C/W
R _{0JB}	Junction-to-board thermal resistance	41.5	°C/W
Y _{JT}	Junction-to-top characterization parameter	4.5	°C/W
Y _{JB}	Junction-to-board characterization parameter	41.5	°C/W
R _{0JC(bottom)}	Junction-to-case (bottom) thermal resistance	20.1	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics app report.



5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)⁽¹⁾ (2)

					Operat tempe			
	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	-40°0	C to 125°C	;	UNIT
					MIN	MIN TYP M		
V _{IL}	Data Input_Negative threshold	Data inputs, OE	1.14 V - 3.6 V	1.14 V - 3.6 V			0.3× VCCA	V
V _{IH}	Data Input_Positive threshold	Data inputs, OE	1.14 V - 3.6 V	1.14 V - 3.6 V	0.7× VCCA			V
		I _{OH} = –3 mA	1.14 V	1.14 V		0.9		
	High-level output	I _{OH} =8 mA	1.65 V	1.65 V	1.1	<u> </u>		V
V _{OH}	voltage ⁽³⁾	I _{OH} = –9 mA	2.3 V	2.3 V	1.8	0		V
		I _{OH} = –12 mA	3 V	3 V	2.4	0		
		I _{OL} = 3 mA	1.14 V	1.14 V		0.1		
	Low-level output	I _{OL} = 8 mA	1.65 V	1.65 V			0.27	.,
V _{OL}	voltage ⁽⁴⁾	I _{OL} = 9 mA	2.3 V	2.3 V			0.23	V
		I _{OL} = 12 mA	3 V	3 V			0.26	
I	Input leakage current	Data Inputs (Ax, Bx) V _I = V _{CCI} or GND	1.14 V - 3.6 V	1.14 V - 3.6 V	9 -1		1	μA
	Partial power down	A Port or B Port	0 V	0 V - 3.6 V	-5		3.6	
l _{off}	current	V _I or V _O = 0 V - 3.6 V	0 V - 3.6 V	0 V	-5		3.6	μA
I _{OZ}	Tri-state output current ⁽⁵⁾	A or B Port: $V_I = V_{CCI}$ or GND $V_O = V_{CCO}$ or GND $\overline{OE} = V_{IH}$	3.6 V	3.6 V	-5		5	μΑ
			1.14 V - 3.6 V	1.14 V - 3.6 V			14	
I _{CCA}	V _{CCA} supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	3.6 V	0 V			11	μA
		10 - 0	0 V	3.6 V	-1			
			1.14 V - 3.6 V	1.14 V - 3.6 V			14	
I _{CCB}	V _{CCB} supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	3.6 V	0 V	-1			μA
		10 - 0	0 V	3.6 V			11	
I _{CCA} + I _{CCB}	Combined supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	1.14 V - 3.6 V	1.14 V - 3.6 V			22	μA
C _i	Control Input Capacitance	V ₁ = 3.3 V or GND	3.3 V	3.3 V			3.9	pF
C _{io}	Data I/O Capacitance	$\overline{OE} = V_{CCA}, V_O = 1.65V$ DC +1 MHz -16 dBm sine wave	3.3 V	3.3 V			2.7	pF

(1) (2) (3)

 V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port. Tested at $V_I = V_{IH.}$ Tested at $V_I = V_{IL.}$ For I/O ports, the parameter I_{OZ} includes the input leakage current. (4) (5)



5.6 Switching Characteristics, V_{CCA} = $1.2 \pm 0.06 V$ Over the recommended temperature range at C_L = 5 pF, unless otherwise indicated.

				B-Port Supply Voltage (V _{CCB})						
PARAMETER		FROM	то	1.2V ± 0.06	1.8 ± 0.15 V	2.5 ± 0.2 V	3.3 ± 0.3 V	UNIT		
				TYP	TYP	TYP	TYP			
t _{pd}	Propagation delay	A	В	4.5	3.0	2.5	2.5	ns		
t _{dis}	Disable time	ŌĒ	В	7.5	6.5	6.0	6.0	ns		
t _{en}	Enable time	ŌĒ	В	9	7	6.5	6.5	ns		
T _R	Rise time ⁽¹⁾	A	В	0.75	0.40	0.30	0.25	ns		
T _F	Fall time ⁽¹⁾	A	В	0.65	0.40	0.30	0.30	ns		
Duty Cycle	Duty cycle variation	A	В	50	50	50	50	%		

(1) Rise and fall time is measured at 20% - 80%



5.7 Switching Characteristics, V_{CCA} = 1.8 ± 0.15 V

Minimum and maximum limits apply over the recommended temperature range at C_L = 15 pF and 250 Mbps, unless otherwise indicated.

				B-Port Supply Voltage (V _{CCB})									
	PARAMETER	FROM	то	1.	8 ± 0.15 \	/	2.	.5 ± 0.2 V	'	3.	.3 ± 0.3 V		UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t _{pd}	Propagation delay	A	В	1.5		4.8	1.2		3.5	1.2		3.0	ns
t _{dis}	Disable time	ŌĒ	В	3.5		7.0	3.0		5.5	3.6		6.5	ns
t _{en}	Enable time	ŌĒ	В	1.2		4.0	1.0		3.0	1.0		2.6	ns
t _{sко}	Output channel-to- channel skew ⁽¹⁾	A	В	-450		450	-300		300	-330		330	ps
T _R	Rise time ⁽²⁾	A	В	0.49		1.35	0.40		0.95	0.35		0.80	ns
T _F	Fall time ⁽²⁾	А	В	0.45		1.35	0.35		0.95	0.35		0.80	ns
Duty Cycle	Duty cycle variation	А	В	47	50	56	47	50	54	47	50	54	%
T _{R_5pF}	Rise time ^{(2) (3)}	A	В	0.28		0.75	0.22		0.55	0.19		0.45	ns
T _{F_5pF}	Fall time ^{(2) (3)}	A	В	0.27		0.75	0.20		0.55	0.18		0.40	ns
t _{SKO_5} pF	Output channel-to- channel skew ^{(1) (3)}	A	В	-300		300	-270		270	-310		310	ps
Duty Cycle _5pF	Duty cycle variation ⁽³⁾	A	в	47	50	54	47	50	54	47	50	54	%
t _{jit(pp)}	Peak-to-peak jitter (250 Mbps 2 ¹⁵ - 1 PRBS input)	A	в	160		450	130	R	335	120		390	ps

(1) Skew parameter also includes jitter

(2) Rise and fall time is measured at 20% - 80%

(3) Parameters tested under RGMII input transition (≤ 2 ns/V) rise and fall time. C_{LOAD} = 5pF



5.8 Switching Characteristics, V_{CCA} = 2.5 ± 0.2 V

Minimum and maximum limits apply over the recommended temperature range at C_L = 15 pF and 250 Mbps, unless otherwise indicated.

				B-Port Supply Voltage (V _{CCB})									
	PARAMETER	FROM	то	1.	8 ± 0.15 \	/	2.	.5 ± 0.2 V		3.	.3 ± 0.3 V		UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t _{pd}	Propagation delay	A	В	1.5		4.2	1.2		3.0	1.1		2.5	ns
t _{dis}	Disable time	ŌE	В	3.6		6.5	2.7		5.0	3.6		6.0	ns
t _{en}	Enable time	ŌE	В	1.2		3.5	1.0		2.5	0.9		2.0	ns
t _{sко}	Output channel-to- channel skew ⁽¹⁾	A	в	-330		330	-200		200	-200		200	ps
T _R	Rise time ⁽²⁾	A	В	0.50		1.4	0.40		1.0	0.35		0.80	ns
T _F	Fall time ⁽²⁾	A	В	0.45		1.4	0.35		1.0	0.30	-	0.80	ns
Duty Cycle	Duty cycle variation	А	в	47	50	55	47	50	53	47	50	53	%
T _{R_5pF}	Rise time ^{(2) (3)}	A	В	0.25		0.75	0.20		0.55	0.15		0.45	ns
T _{F_5pF}		A	В	0.25		0.76	0.2		0.55	0.15		0.45	ns
t _{SKO_5} pF	Output Channel-to- channel skew ^{(1) (3)}	A	В	-210		210	-160		160	-180		180	ps
Duty Cycle _5pF	Duty cycle variation ⁽³⁾	A	в	48	50	53	48	50	52	48	50	52	%
t _{jit(pp)}	Peark-to-peak jitter (250 Mbps 2 ¹⁵ - 1 PRBS input)	A or B	A or B	120		370	100	2	300	90		360	ps

(1) Skew parameter also includes jitter

(2) Rise and fall time is measured at 20% - 80%

(3) Parameters tested under RGMII input transition (≤ 2 ns/V) rise and fall time. C_{LOAD} = 5 pF



5.9 Switching Characteristics, V_{CCA} = 3.3 ± 0.3 V

Minimum and maximum limits apply over the recommended temperature range at C_L = 15 pF and 250 Mbps, unless otherwise indicated.

				B-Port Supply Voltage (V _{CCB})									
	PARAMETER FROM 1		то	1.8 ± 0.15 V		2.5 ± 0.2 V			3.3 ± 0.3 V		UNIT		
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t _{pd}	Propagation delay	A	В	1.2		3.8	1.2		2.7	1.1		2.3	ns
t _{dis}	Disable time	ŌE	A	2.7		7.0	2.7		7.0	2.7		7.0	ns
t _{en}	Enable time	ŌĒ	A	0.75		4.0	0.75		4.0	0.75		4.0	ns
t _{sко}	Output channel-to- channel skew ⁽¹⁾	A	В	-310		310	-190		190	-160		160	ps
T _R	Rise time ⁽²⁾	A	В	0.50		1.3	0.40		1.0	0.35		0.80	ns
T _F	Fall time ⁽²⁾	A	В	0.45		1.3	0.35		1.0	0.35	-	0.80	ns
Duty Cycle	Duty cycle variation	А	В	46	50	54	48	50	53	48	50	52	%
T _{R_5pF}	Rise time ^{(2) (3)}	A	В	0.30		0.80	0.20		0.55	0.15		0.45	ns
T _{F_5pF}	Fall time ^{(2) (3)}	A	В	0.25		0.80	0.20		0.60	0.20		0.45	ns
t _{SKO_5} pF	Output channel-to- channel skew ^{(1) (3)}	A	В	-230		230	-130		130	-140		140	ps
Duty Cycle _5pF	Duty cycle variation ⁽³⁾	A	в	48	50	53	48	50	52	48	50	52	%
t _{jit(pp)}	Peark-to-peak jitter (250 Mbps 2 ¹⁵ - 1 PRBS input)	A or B	A or B	115		390	75	R	330	75		330	ps

(1) Skew parameter also includes jitter

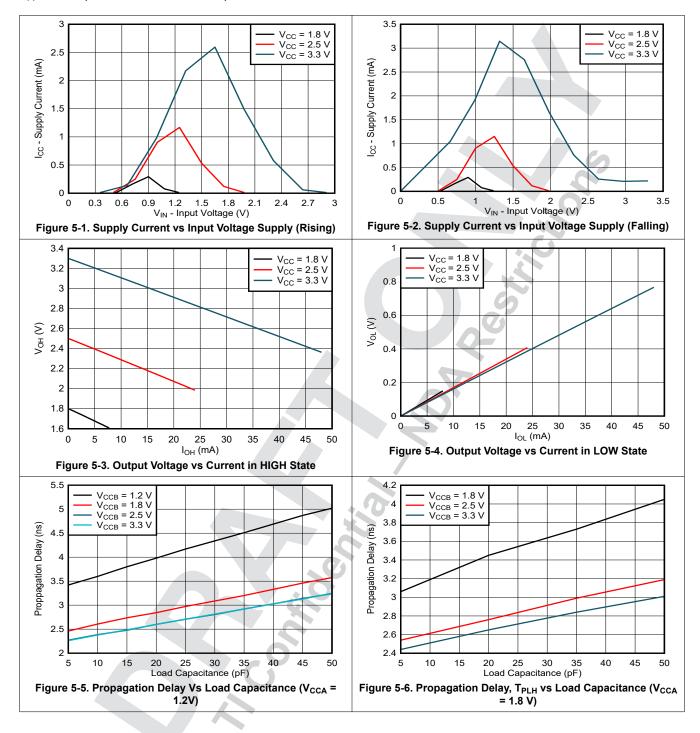
(2) Rise and fall time is measured at 20% - 80%

(3) Parameters tested under RGMII input transition (≤ 2 ns/V) rise and fall time. C_{LOAD} = 5 pF

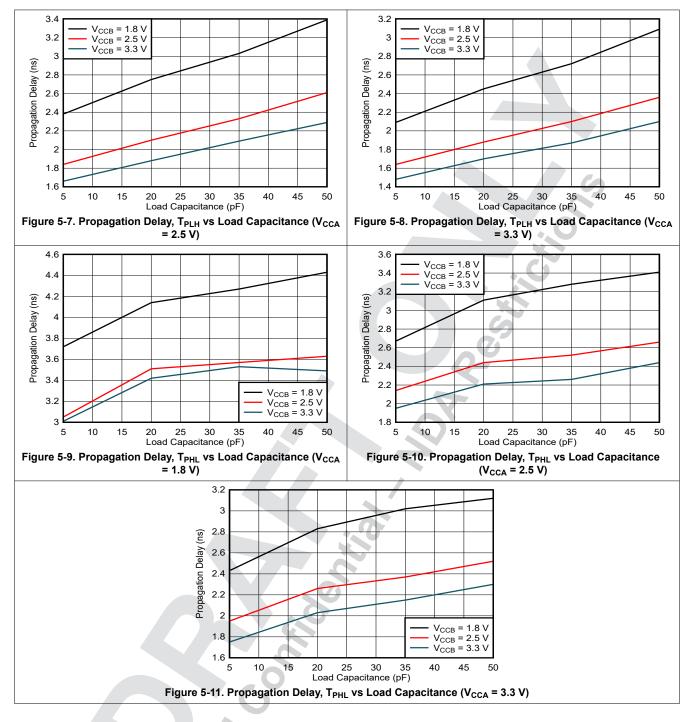


5.10 Typical Characteristics

 $T_A = 25^{\circ}C$ (unless otherwise noted)



5.10 Typical Characteristics (continued)



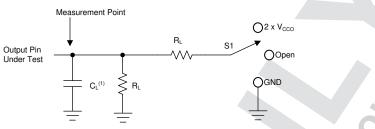


6 Parameter Measurement Information

6.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f = 1 MHz
- Z_O = 50 Ω
- Δt/ΔV ≤ 1 ns/V

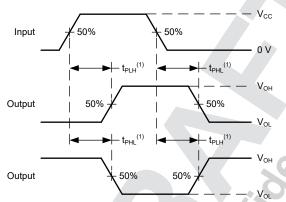


A. C_L includes probe and jig capacitance.

Figure 6-1. Load Circuit

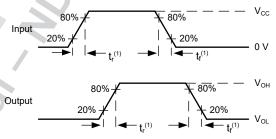
	Parameter	V _{cco}	RL	CL	S ₁	V _{TP}		
t _{pd}	Propagation (delay) time	1.14 V – 3.6 V	2 kΩ	15 pF	Open	N/A		
t _{en} , t _{dis}	Enable time, disable time	1.14 V – 3.6 V	2 kΩ	15 pF	2 × V _{CCO}	0.15 V		
t _{en} , t _{dis}	Enable time, disable time	1.14 V – 3.6 V	2 kΩ	15 pF	GND	0.15 V		





- 1. The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .
- 2. V_{OH} and V_{OL} are typical output voltage levels that occur with specified R_L, C_L, and S₁

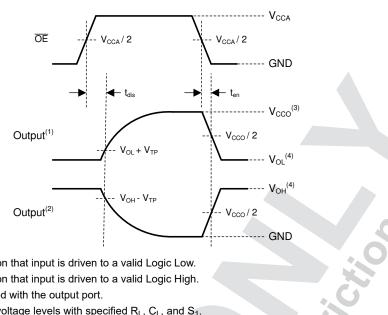
Figure 6-2. Propagation Delay



1. V_{OH} and V_{OL} are typical output voltage levels that occur with specified R_L , C_L , and S_1

Figure 6-3. Input Transition Rise and Fall Rate





- Output waveform on the condition that input is driven to a valid Logic Low. Α.
- Output waveform on the condition that input is driven to a valid Logic High. Β.
- V_{CCO} is the supply pin associated with the output port. C.
- D. V_{OH} and V_{OL} are typical output voltage levels with specified RL, CL, and S1.

Figure 6-4. Enable Time and Disable Time



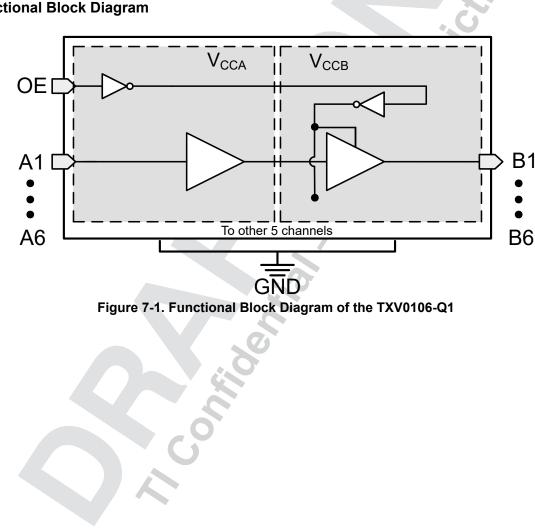
7 Detailed Description

7.1 Overview

The TXV0106-Q1 is an 6-bit translating transceiver that uses two individually configurable power-supply rails. The device is operational with both V_{CCA} and V_{CCB} supplies as low as 1.14 V and as high as 3.6 V. Additionally, the device can be used as a buffer with $V_{CCA} = V_{CCB}$. The Ax port is designed to track V_{CCA} , and the Bx port is designed to track V_{CCB}.

The TXV0106-Q1 device is designed for asynchronous communication between data buses, and transmits data in a fixed direction from the A bus to the B bus. The output-enable input (OE) is used to disable the outputs so the buses are effectively isolated. The output-enable pin (\overline{OE}) of the TXV0106-Q1 is referenced to V_{CCA}. To enable the high-impedance state of the level shifter I/Os during power up or power down, the OE pin should be tied to V_{CCA} through a pullup resistor.

This device is fully specified for partial-power-down applications using the Ioff current. The Ioff protection circuitry prevents excessive current from being drawn from or sourced into an input, output, or I/O while the device is powered down.



7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

7.3.2 Partial Power Down (I_{off})

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

7.3.3 V_{CC} Isolation and V_{CC} Disconnect (I_{off-float})

This device has 2 features V_{CC} Isolation and V_{CC} Disconnect which helps in preventing current backflow in case the device is powered down unexpectedly. V_{CC} Isolation occurs when one of the supplies is kept at (or goes to) zero during normal operation, no current will be consumed by the supply that is maintained. This scenario forces all I/Os to be High-Z. V_{CC} Disconnect occurs when one of the supplies is left floating (disconnects) after ramping up, the I/Os are forced into High-Z without consuming any current from the maintained supply. In both cases, the I/Os will enter a high-impedance state when either supply (V_{CCA} or V_{CCB}) is < 100 mV or left floating, while the other supply is still connected to the device. See Figure 8-2 for a visual representation.

The maximum supply current is specified by I_{CCx} , while V_{CCx} is floating, in the *Electrical Characteristics*. The maximum leakage into or out of any input or output pin on the device is specified by $I_{off(float)}$ in the *Electrical Characteristics*.

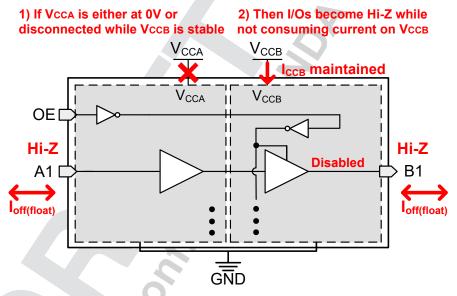


Figure 7-2. V_{CC} Disconnect and V_{CC} Isolation Feature

7.3.4 Over-Voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Recommended Operating Conditions*.

7.3.5 Negative Clamping Diodes

The inputs and outputs to this device have negative clamping diodes as depicted in Figure 7-3



CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

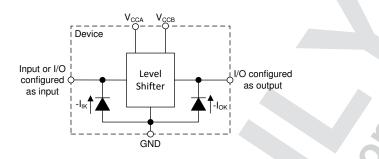


Figure 7-3. Electrical Placement of Clamping Diodes for Each Input and Output

7.3.6 Fully Configurable Dual-Rail Design

Both the V_{CCA} and V_{CCB} pins can be supplied at any voltage from 1.14 V to 3.6 V, making the device an excellent choice for translating between any of the voltage nodes (1.2 V, 1.8 V, 2.5 V, and 3.3 V).

7.3.7 Supports High-Speed Translation

The TXV0106-Q1 device can support high data rate applications. The translated signal data rate can support up to 500Mbps when the signal is translated from 1.65 V to 3.6 V. For the device to meet RGMII 2.0 timing specifications (rise or fall time, skew, and duty cycle distortion) the data rate will need to be lowered to 250Mbps.

7.3.8 Wettable Flanks

Wettable flanks help improve side wetting after soldering which makes QFN packages easier to inspect with automatic optical inspection (AOI). A wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet as shown in the figure. Please see the mechanical drawing for additional details.

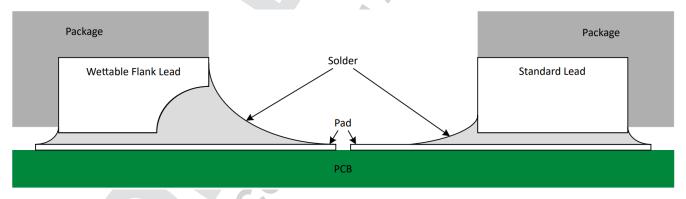


Figure 7-4. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

7.3.9 Integrated Damping Resistor and Impedance Matching

The TXV0106-Q1 features a 10 Ω integrated damping resistor to help minimize signal reflections on the rising and falling edges. If impedance matching with a 50 Ω load is required, then a series resistor will be needed. Since the output impedance of the device will vary with the output voltage, (V_{CCB}), Table 8-1 provides the recommended resistor values needed to impedance match a 50 Ω load

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Table 7-1. Series Resistor Values for 50 Ω Impedance Matching

Output Voltage (V _{CCB})	1.2 V	1.8 V	2.5 V	3.3 V
Series Resistor	53 Ω	25 Ω	30 Ω	32 Ω

7.4 Device Functional Modes

Table 7-2. Function Table

CONTROL INPUTS (1)	PORTS	TATUS	OPERATION
ŌĒ	A PORT	B PORT	
L	Input (Hi-Z)	Output (Enabled)	A data to B bus
Н	Input (Hi-Z)	Input (Hi-Z)	Isolation

(1) Input circuits of the data I/Os are always active and should be kept at a valid logic level.



8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TXV0106-Q1 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The TXV0106-Q1 device is an excellent choice for use in applications where a push-pull driver is connected to the data I/Os. The maximum data rate can be up to 500Mbps when device translates a signal from 1.65 V to 3.6 V.

8.2 Typical Application

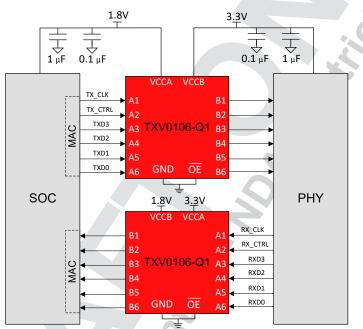


Figure 8-1. RGMII Application (Interfacing Between MAC and PHY)

8.2.1 Design Requirements

For this design example, use the parameters listed in Table 8-1.

Table 8-1. Design Parameters

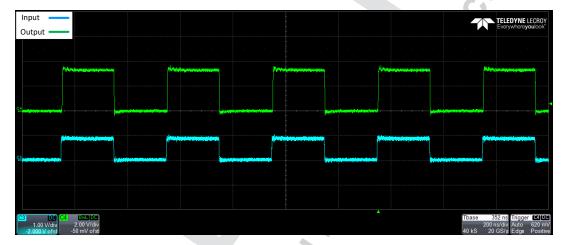
DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	1.65 V to 3.6 V
Output voltage range	1.65 V to 3.6 V
Frequency	125 MHz
Load Capacitance	5 pF
Input Transition Rise/Fall Time	< 2 ns/V



8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range:
 - Use the supply voltage of the device that is driving the TXV0106-Q1 device to determine the input voltage range. For a valid logic-high, the value must exceed the positive-going input-threshold voltage (V_{t+}) of the input port. For a valid logic low the value must be less than the negative-going input-threshold voltage (V_{t-}) of the input port.
- Output voltage range:
 - Use the supply voltage of the device that the TXV0106-Q1 device is driving to determine the output voltage range.
- RGMII timing:
 - For the TXV0106-Q1 to meet RGMII timing specifications, parameters like frequency, C_{LOAD} and input rise/fall transition have to be met. Ensure each channel does not exceed a maximum frequency of 125 MHz, use a C_{LOAD} no greater than 5 pF, and use an input rise or fall transition no greater than 2 ns/V.



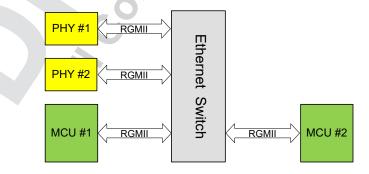
8.2.3 Application Curves

Figure 8-2. Up Translation (1.8 V to 3.3 V) C_{LOAD} = 15 pF at 2.5 MHz

8.3 System Examples

8.3.1 Solving Power Sequencing Challenges with the TXV0106-Q1

The TXV0106-Q1 not only solves voltage mismatch between interfaces but also solves power sequencing challenges. In some Ethernet applications, you may have a multi-core RGMII system with an Ethernet switch Figure 8-3. In other applications, you may have a standard Ethernet interface with one MAC and PHY. In either case, it is necessary to power up each device properly. This will prevent the I/O pins from powering up before the core blocks, which can cause in-rush current during power up or bus contention and other malfunctions.







Low Dropout (LDO) devices are a common way to power up devices, but they do not provide any power sequencing features. As can be seen in Figure 8-4, before the 1.8 V can be applied to the MAC, the input of the LDO will need to come up first. This will result in the PHY powering up which can lead to in-rush current flowing into the MAC I/O pins.

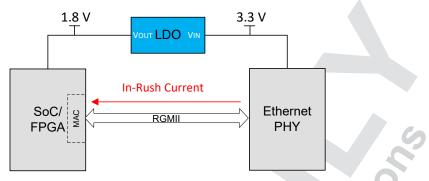


Figure 8-4. Residual Current Flowing Into MAC I/O Pins After PHY is Powered Up

With the TXV0106-Q1 supporting the $I_{off-float}$ feature, in-rush current from improper power sequencing can be prevented. When either power supply pin is at 0 V or below 100 mV, the I/O pins become high impedance until both pins go above 100 mV. The high impedance state will prevent any in-rush current from flowing to the opposite side.

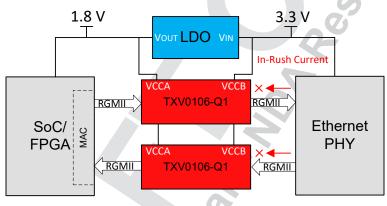


Figure 8-5. Using the TXV0106-Q1 for Power Isolation

For additional information on the TXV0106-Q1 and power isolation use cases, see the *Solving Power Sequencing Challenges for Ethernet RGMII Communications* application note.

8.4 Power Supply Recommendations

The TXV0106-Q1 uses two separate configurable power supply rails, V_{CCA} and V_{CCB} . The A port and B port are designed to track V_{CCA} and V_{CCB} , respectively, allowing for low-voltage fixed translation between any of the 1.2-V, 1.8-V, 2.5-V and 3.3-V voltage nodes.

The output-enable \overline{OE} input circuit is designed to be supplied by V_{CCA} . When the \overline{OE} input is high, all outputs are placed in the high-impedance state. To put the outputs in a high-impedance state during power up or power down, tie the \overline{OE} input pin to V_{CCA} through a pullup resistor and do not be enable it until V_{CCA} and V_{CCB} are fully ramped and stable. The current-sinking capability of the driver determines the minimum value of the pullup resistor to V_{CCA} .



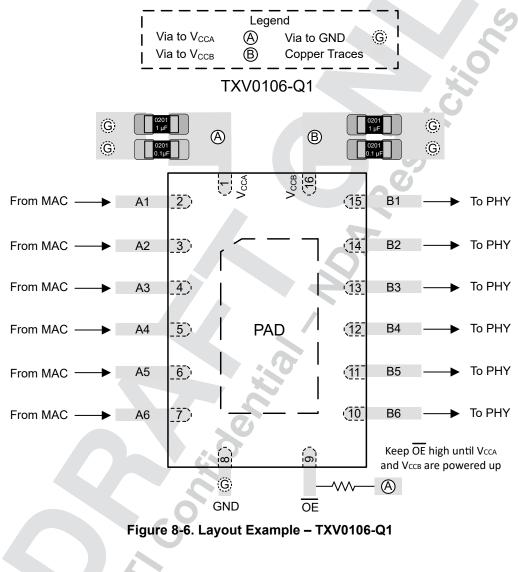
8.5 Layout

8.5.1 Layout Guidelines

For device reliability, it is recommended to follow common printed-circuit board layout guidelines such as:

- · Use short trace lengths to avoid excessive loading.
- Use bypass capacitors on the power supply pins and place them as close to the device as possible.
- A 0.1-μF bypass capacitor is recommended, but transient performance can be improved by having both 1-μF and 0.1-μF capacitors in parallel with the smallest value capacitor placed closest to the power pin.
- The high drive capability of this device creates fast edges into light loads. Routing and load conditions should be considered to prevent ringing.

8.5.2 Layout Example





9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

 Texas Instruments, Solving Power Sequencing Challenges for Ethernet RGMII Communications application note

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	Changes from Revision A (December 2023) to Revision B (February 2024)	Page
•	Added 1.14V Test Conditions to Recommended Operating Conditions Table	5
•	Added 1.14V Test Conditions to Electrical Characteristics Table	6
•	Added 1.2V Switching Characteristics Table	7

С	hanges from Revision * (August 2023) to Revision A (December 2023)	Page
•	Changed the status of the data sheet from: Advanced Information to: Production Data	1

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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